

# NCE N-Channel Enhancement Mode Power MOSFET

# **Description**

The NCE4003A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. This device is suitable for use as a Battery protection or in other switching application.

#### **General Features**

● V<sub>DS</sub> =40V,I<sub>D</sub> =3A

 $R_{DS(ON)} = 32m\Omega @ V_{GS} = 10V(Typ)$ 

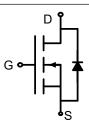
 $R_{DS(ON)} = 43m\Omega @ V_{GS}=4.5V(Typ)$ 

 $R_{DS(ON)} = 82m\Omega @ V_{GS}=2.5V(Typ)$ 

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

# **Application**

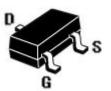
- Battery switch
- ●DC/DC converter



#### **Schematic Diagram**



**Marking and Pin Assignment** 



**SOT-23 Top View** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
4003A	NCE4003A	SOT-23	Ø180mm	8 mm	3000 units

## Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	40	V
Gate-Source Voltage	VGS	±20	V
Drain Current-Continuous	I <sub>D</sub>	3	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	10	Α
Single pulse avalanche energy (Note 5)	Eas	15	mJ
Maximum Power Dissipation	P <sub>D</sub>	0.7	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	179	°C/W



# Electrical Characteristics (T<sub>A</sub>=25°Cunless otherwise noted)

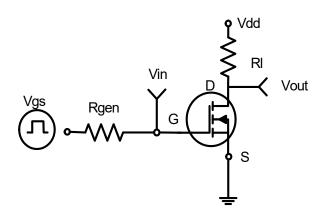
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	,					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.7	1.0	1.5	V
		V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	32	38	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	-	43	53	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1A	-	82	106	mΩ
Forward Transconductance	<b>g</b> FS	$V_{DS}=5V,I_{D}=3A$	-	6	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ 00\/\/ 0\/	-	265	-	PF
Output Capacitance	Coss	$V_{DS}=20V, V_{GS}=0V,$	-	35	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz - 32		-	PF	
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =20 $V$ , $I_{D}$ =3 $A$	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{GEN}$ =1 $\Omega$	-	12	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg	\/ 00\/ L 0A	-	10.2	-	nC
Gate-Source Charge	Qgs	$V_{DS}=20V,I_{D}=3A,$	-	1.7	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	2.1	-	nC
Drain-Source Diode Characteristics	,		•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3	Α

## Notes:

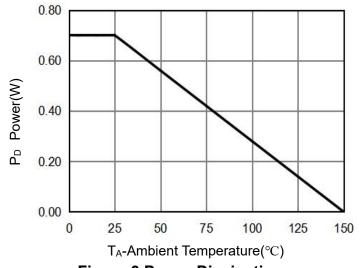
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- **4.** Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=20V,VG=10V,L=0.5mH,Rg=25 $\Omega$



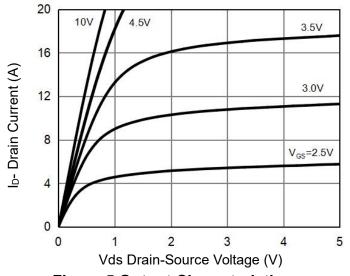
# **Typical Electrical and Thermal Characteristics**



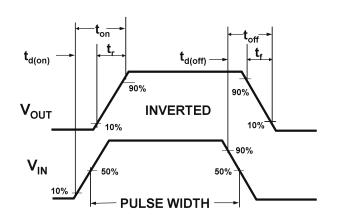
**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 



**Figure 2:Switching Waveforms** 

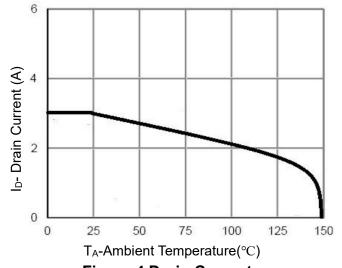


Figure 4 Drain Current

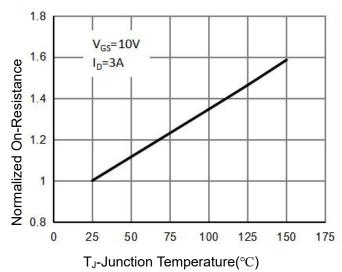
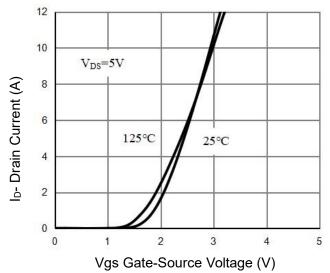


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 

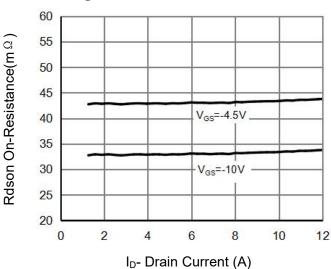


Figure 9 Drain-Source On-Resistance

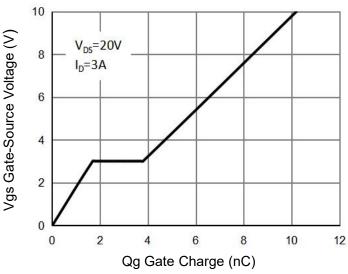
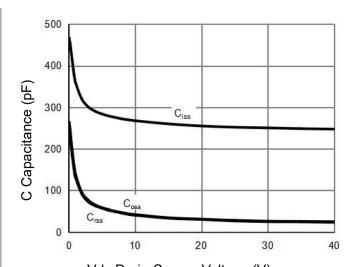


Figure 11 Gate Charge



Vds Drain-Source Voltage (V)



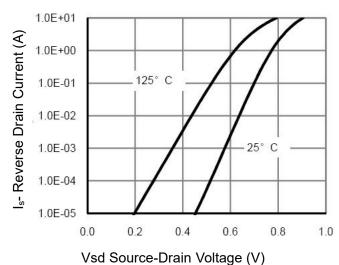


Figure 10 Source- Drain Diode Forward

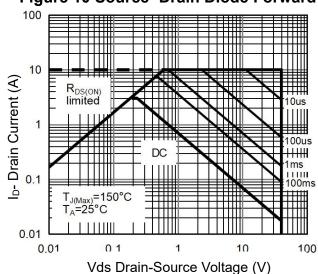
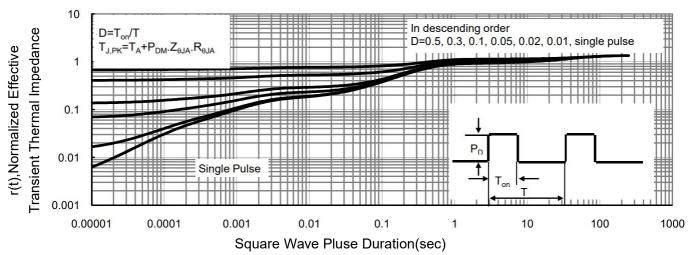


Figure 12 Safe Operation Area

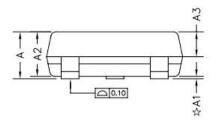


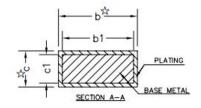


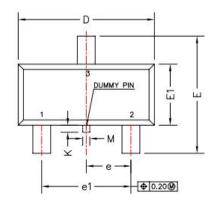
**Figure 13 Normalized Maximum Transient Thermal Impedance** 

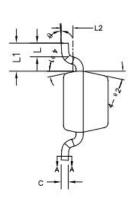


# **SOT-23 Package Information**









Cumbal	Millimeters			
Symbol	Min.	Max.		
Α	0.89	1.12		
A1	0.01	0.10		
A2	0.88	1.02		
A3	0.43	0.63		
b	0.36	0.50		
b1	0.35	0.45		
С	0.14	0.20		
c1	0.14	0.16		
D	2.80	3.00		
E	2.35	2.64		
E1	1.20	1.40		
е	0.90	1.00		
e1	1.80	2.00		
L	0.40	0.60		
L1	0.6	REF		
L2	0.25BSC			
М	0.10	0.25		
K	0.00	0.25		
θ	0°	8°		
θ1	10°	14°		
θ2	10°	14°		



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